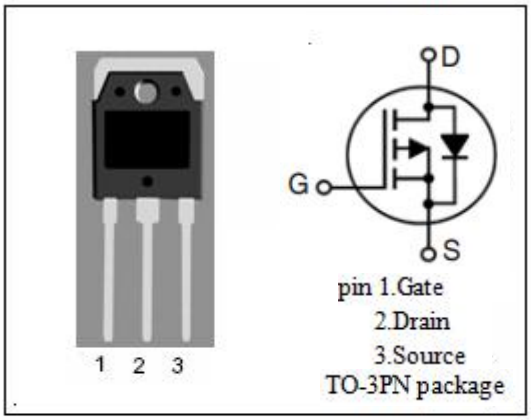
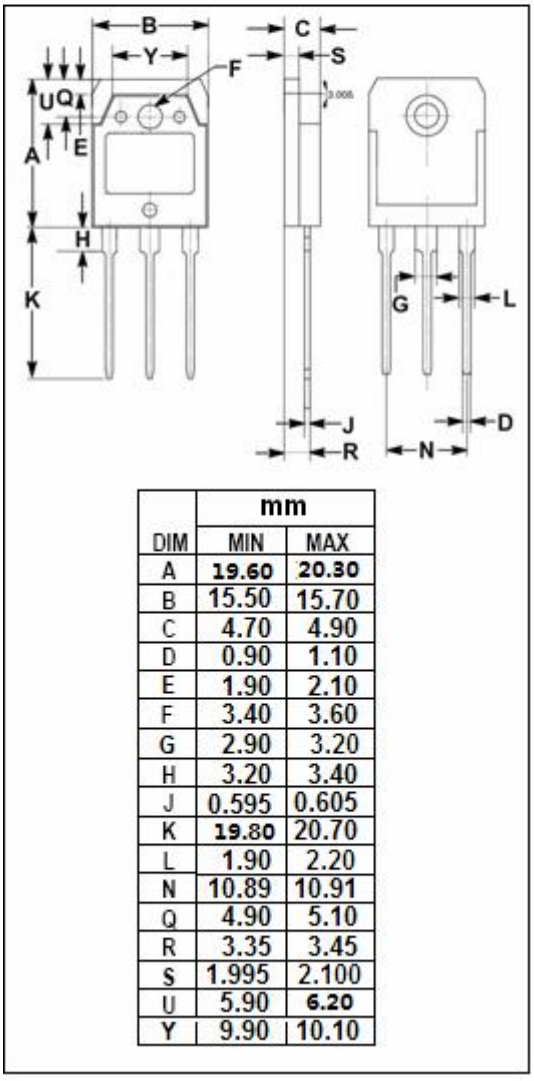
isc P-Channel MOSFET Transistor IXTQ52P10P



- **FEATURES**
- Drain Source Voltage-
  : V_{DSS}= -100V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ ≤50mΩ @V_{GS}= -10V
- Fast Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

- **APPLICATIONS**
- Easy to Mount
- Space Savings
- High Power Density



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage-Continuous	±20	V
I_D	Drain Current-Continuous	-52	A
I_{DM}	Drain Current-Single Plused	-130	A
P_D	Total Dissipation @T_C=25℃	300	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	0.42	℃/W

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• ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= -250uA	-100			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= -250uA	-2		-4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D= -26A			50	mΩ
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V;V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -100V; V_{GS}= 0 V_{DS}= -100V; V_{GS}= 0;T_J=125℃			-10 -150	μA
V_{SD}	Diode Forward On-voltage	I_F= -26A ;V_{GS}= 0			-3.5	V